



## Improved mechanical properties of dense $\beta$ - $\text{Si}_3\text{N}_4$ ceramics fabricated by spark plasma sintering with $\text{Al}_2\text{O}_3$ -YSZ additives

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### Abstract

*In this work the influence of sintering conditions on structure and mechanical properties of  $\text{Si}_3\text{N}_4$  ceramics was investigated. Nearly full dense  $\beta$ - $\text{Si}_3\text{N}_4$  ceramics with excellent mechanical properties and interlock microstructure of elongated grains was fabricated using  $\text{Al}_2\text{O}_3$  and yttria-stabilized zirconia (YSZ with 3 mol%  $\text{Y}_2\text{O}_3$ ) as sintering additives by spark plasma sintering (SPS) at relatively low temperature of 1600 °C for 15 min. X-ray diffraction analysis shows that the SPSed sample is pure  $\beta$ - $\text{Si}_3\text{N}_4$  phase without any secondary crystalline phase. The elements Al, Zr, Y and O of the additive can diffuse into  $\text{Si}_3\text{N}_4$  lattice forming  $\beta$ - $\text{Si}_3\text{N}_4$ -based solid solution. The residual additive formed an amorphous phase at the  $\beta$ - $\text{Si}_3\text{N}_4$  grain boundaries. The  $\beta$ - $\text{Si}_3\text{N}_4$  ceramics obtained by SPS using 6.0 wt.%  $\text{Al}_2\text{O}_3$  and 6.0 wt.% YSZ as additives shows interlock elongated  $\beta$ - $\text{Si}_3\text{N}_4$  grains of 500 nm in width and 3000 nm in length, high density of 3.29 g/cm<sup>3</sup>, Vickers hardness of 16.15 GPa and high fracture toughness  $K_{IC}$  of 6.75 MPa m<sup>1/2</sup>.*

**Keywords:**  $\text{Si}_3\text{N}_4$ , spark plasma sintering, sintering additives, mechanical properties, microstructure

### I. Introduction

Advanced ceramics and their composites have been developed for a number of commercial and industrial applications, such as turbine engines, electronic packaging and cutting tools [1–5]. Silicon nitride is one of the most promising advanced ceramics materials due to its low density, high temperature strength, excellent thermal shock resistance, which can be widely used in cutting tools, bearings, reciprocating engine parts, wear and metal forming components and springs [6–8]. Two phase structures exist in  $\text{Si}_3\text{N}_4$  ceramics, the low temperature structure  $\alpha$ - $\text{Si}_3\text{N}_4$  and the high temperature structure  $\beta$ - $\text{Si}_3\text{N}_4$  [9]. The large, elongated  $\beta$ - $\text{Si}_3\text{N}_4$  grains with high aspect ratio deflect the propagation of cracks, and thus increase the fracture toughness of the material [10]. Therefore, manufacturing of the dense  $\beta$ - $\text{Si}_3\text{N}_4$  with interlocking microstructures of elongated grains plays an important role in the high mechanical properties of silicon nitride ceramics for many

structural applications [11].

$\text{Si}_3\text{N}_4$  is difficult to densify by solid state sintering because of its high degree of covalent bonding, thus liquid-phase sintering with suitable additives is a preferred method of promoting densification. Various metal oxides such as lanthanide oxides and rare earth oxides were used as sintering additives. Conventional sintering techniques, such as pressureless sintering [12], reaction bonding sintering [13], gas pressure sintering [14], hot pressing sintering [15] and hot isostatic pressing sintering etc. [16], usually need high sintering temperature, slow heating rate and long holding time to obtain fully dense materials and fabricate silicon nitride ceramics with sintering additives. Spark plasma sintering (SPS) is known for its high efficiency to densify ceramics at relatively low temperature under compression, using pulsed DC current through punches and graphite die. The pulsed DC current promotes a fast heating of the powder by charging the intervals between powder particles with electrical energy and effectively applying a high-temperature spark plasma. It is one of the most innovative and promising methods for producing silicon nitride [17]. It has been reported that SPS has

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been used to fabricate highly dense  $\beta$ - $\text{Si}_3\text{N}_4$ , at 1600 °C for 5 min [18], at 1500 °C for 5 min [19] or at 1700 °C for 5 min [20], using  $\text{Y}_2\text{O}_3$  and  $\text{Al}_2\text{O}_3$  as sintering additives, or at 1700 °C for 5 min using  $\text{BaCO}_3$ ,  $\text{SiO}_2$  and  $\text{Al}_2\text{O}_3$  as sintering additives [21]. The composites in  $\text{ZrO}_2$ - $\text{Al}_2\text{O}_3$  system have the potential to combine an increased hardness with excellent toughness of tetragonal zirconia. The equimolecular mixtures of  $\alpha$ - and  $\beta$ - $\text{Si}_3\text{N}_4$  with high density, Vickers hardness of 6–12 GPa and fracture toughness of 3.7–6.2  $\text{MPa m}^{1/2}$  were fabricated by hot-pressing using  $\text{ZrO}_2$  and  $\text{Al}_2\text{O}_3$  as sintering additives [22].

In this work, a nearly full dense  $\beta$ - $\text{Si}_3\text{N}_4$  ceramics with interlock microstructure of elongated grains, showing good Vickers hardness of 16.15 GPa and fracture toughness  $K_{IC}$  of 6.75  $\text{MPa m}^{1/2}$ , was fabricated using  $\text{Al}_2\text{O}_3$  and yttria-stabilized zirconia (YSZ with 3 mol%  $\text{Y}_2\text{O}_3$ ) as sintering additives by spark plasma sintering (SPS) at relative low temperature of 1600 °C for 15 min.

## II. Experimental procedure

$\text{Si}_3\text{N}_4$  (95%  $\alpha$ -phase, SN-E10 grade, 0.6  $\mu\text{m}$ , UBE Industries, Japan),  $\text{Al}_2\text{O}_3$  (Meryer, 100 nm, Germany) and YSZ (3 mol%  $\text{Y}_2\text{O}_3$ , 100 nm, King's Ceramics & Chemicals Co., LTD) powders were used as starting materials in this study. These powders were mixed according to the weight ratios of  $\text{Si}_3\text{N}_4$  :  $\text{Al}_2\text{O}_3$  : YSZ = 88 : 6 : 6 by wet ball-milling in ethanol for 8 h using zirconia balls and high density polyethylene jar. The weight ratio of balls to powders was kept at about 10 : 1. The zirconia balls with 3.5 and 5.0 mm in diameter and their weight ratio of 8 : 2 were used. The milled powders were dried and sintered by SPS (lab-made SPS system) in vacuum lower than  $1.0 \times 10^{-2}$  Pa using a high strength cylindrical graphite die with the inner diameter of 30 mm. The heating process was controlled by an optical pyrometer (Raytek) focused on the surface of the die. The samples were heated to the final sintering temperature, 1450 or 1600 °C, at heating rate of 100 °C/min, held at this temperature for 15 min and then cooled down to room temperature at rate of 100 °C/min. The initial pressure of 15.0 MPa was applied before heating and further pressure of 45 MPa was applied above 1000 °C.

The sintered samples were polished using <1  $\mu\text{m}$  diamond paste. The density of the sintered sample was measured by the Archimedes method. The phases of the samples were analysed by X-ray diffraction (XRD) using a Bruker D8 Advance SS/18 kW diffractometer with  $\text{CuK}\alpha$  radiation and Jade 6.5 software and the microstructures were observed by scanning electron microscopy (SEM) with energy dispersive X-ray spectroscopy (EDS) (Su-70, Hitachi). The Rietveld refinements of XRD patterns, performed by Topas 3.1 software, were used to estimate the theoretical density of the sample. Hardness and fracture toughness were determined using indentation technique. The hardness of the polished surface of the bulk sample was measured on a hardness tester (Micro-586 Vickers Hardness Tester,

Shanghai Tianiin Optical Instrument Co., Ltd.) with an indentation load of 98 N and a dwell time of 15 s. The fracture toughness  $K_{IC}$  was determined from the measurement of the crack length based on the equation [23]:

$$K_{IC} = 0.016 \left( \frac{E}{H} \right)^{1/2} \frac{1000P}{C^{3/2}} \quad (1)$$

where  $K_{IC}$  is fracture toughness,  $E$  is Young's modulus (300 GPa for  $\text{Si}_3\text{N}_4$  in this work [23]),  $H$  is the Vickers hardness,  $P$  is the indentation load and  $C$  is the mean crack length measured from the centre of the indentation.

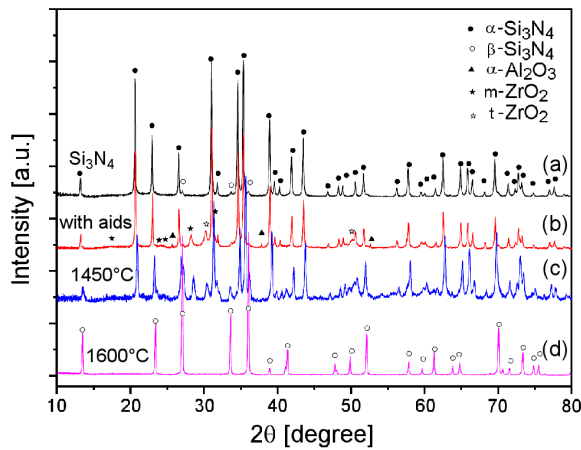
## III. Results and discussion

### 3.1. Densities

A high density of the  $\text{Si}_3\text{N}_4$  ceramics was obtained by SPS using 6.0 wt.%  $\text{Al}_2\text{O}_3$  and 6.0 wt.% YSZ as additives at relatively low temperature, which is important for many structure applications. The density was 3.255  $\text{g/cm}^3$  for the sample SPSed at 1450 °C for 15 min and 3.290  $\text{g/cm}^3$  for the sample SPSed at 1600 °C for 15 min, under the pressure of 45 MPa. This is nearly full density of the  $\text{Si}_3\text{N}_4$ -6.0  $\text{Al}_2\text{O}_3$ -6.0 YSZ composite as compared to its theoretical density of 3.36  $\text{g/cm}^3$ , estimated by Rietveld refinement from its XRD pattern and EDS results. The small amount of Al, Zr and Y was considered to occupy the Si site of  $\beta$ - $\text{Si}_3\text{N}_4$  lattice, while O occupies the N site of  $\beta$ - $\text{Si}_3\text{N}_4$  lattice. The small amount of the glass phase at the grain boundary of  $\beta$ - $\text{Si}_3\text{N}_4$  phase was ignored in this calculation. This density is higher than reported in relative literature. Thus, it is reported that the density of 3.25  $\text{g/cm}^3$  of  $\text{Si}_3\text{N}_4$  ceramics was obtained by SPS using 9.0 wt.%  $\text{Al}_2\text{O}_3$  and 6.0 wt.%  $\text{Y}_2\text{O}_3$  additives at 1650 °C for 10 min [24]. The silicon nitride ceramics obtained by SPS with a density of 3.08  $\text{g/cm}^3$  sintered at 1500 °C, 3.23  $\text{g/cm}^3$  sintered at 1600 °C and also 3.23  $\text{g/cm}^3$  sintered at 1650 °C, by using 2.0 wt.%  $\text{Al}_2\text{O}_3$  and 5.0 wt.%  $\text{Y}_2\text{O}_3$  additive was also reported [25]. Hayashi *et al.* [26] reported that the ceramic material obtained by sintering in a graphite resistance furnace at 1900 °C for 2 to 48 h under a nitrogen pressure of 0.9 MPa had a density ranging from 3.20 to 3.26  $\text{g/cm}^3$  with  $\text{MgSiN}_2$  as an additive. Ewais *et al.* [22] reported that the silicon nitride ceramics obtained by hot pressing sintering at 1800 °C for 20 min under pressure of 30 MPa in  $\text{CO/CO}_2$  atmosphere had a density of 2.93  $\text{g/cm}^3$  by using 5.0 wt.%  $\text{ZrO}_2$  and 5.0 wt.%  $\text{Al}_2\text{O}_3$  as additives and 3.26  $\text{g/cm}^3$  by using 10.0 wt.%  $\text{ZrO}_2$  and 10 wt.%  $\text{Al}_2\text{O}_3$  additive.

### 3.2. Phase and microstructure

Figure 1 shows the XRD patterns for the raw  $\text{Si}_3\text{N}_4$  powders, mixed powders with 6.0 wt.%  $\text{Al}_2\text{O}_3$  and 6.0 wt.% YSZ additives and the samples sintered at 1450 °C and 1600 °C. It is obvious that the raw powder contains  $\alpha$ - $\text{Si}_3\text{N}_4$  main phase with minor  $\beta$ - $\text{Si}_3\text{N}_4$  phase, shown in Fig. 1a. The  $\text{Al}_2\text{O}_3$  and YSZ additive phases,



**Figure 1.** XRD patterns for: a) the raw  $\text{Si}_3\text{N}_4$  powders, b) mixed powders with 6.0 wt.%  $\text{Al}_2\text{O}_3$  and 6.0 wt.% YSZ additives, c) the samples sintered at 1450 °C and d) 1600 °C for 15 min

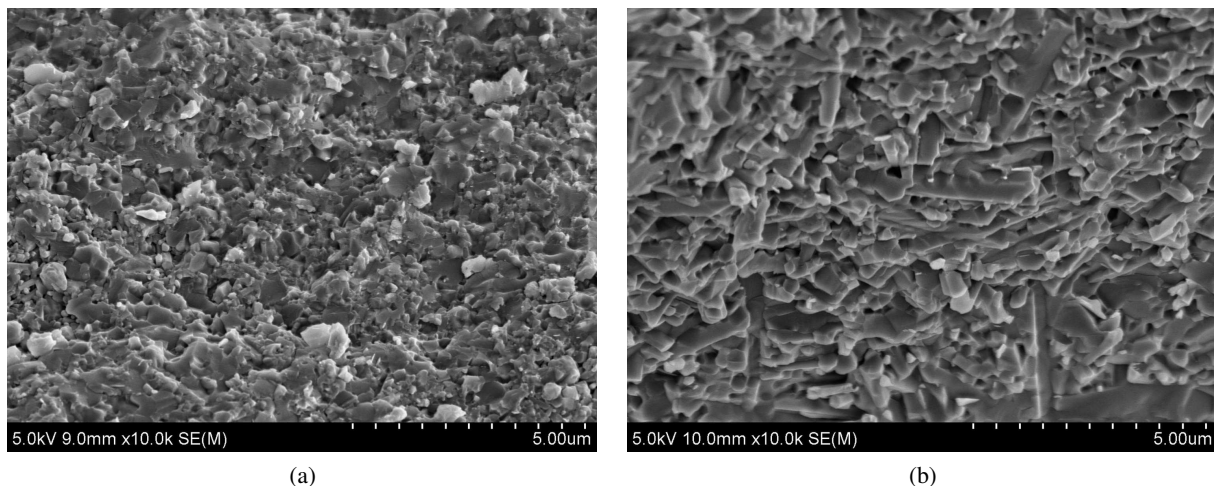
$\alpha$ - $\text{Al}_2\text{O}_3$ , monoclinic (m)  $\text{ZrO}_2$  and tetragonal (t)  $\text{ZrO}_2$ , appear in the mixed powder, shown in Fig. 1b. As the mixed powder was sintered at 1450 °C for 15 min, the amount of  $\beta$ - $\text{Si}_3\text{N}_4$  phase increases, but  $\alpha$ - $\text{Si}_3\text{N}_4$ ,  $\alpha$ - $\text{Al}_2\text{O}_3$ , m- $\text{ZrO}_2$  and t- $\text{ZrO}_2$  phases are kept, shown in Fig. 1c. However, the pure  $\beta$ - $\text{Si}_3\text{N}_4$  phase was obtained without any other crystalline phases in the sample sintered at 1600 °C for 15 min, shown in Fig. 1d.

Figure 2 shows the SEM images for the fracture surfaces of the samples SPSed at 1450 °C and 1600 °C for 15 min. Combining XRD analysis, it is found the typical  $\alpha$ - $\text{Si}_3\text{N}_4$  equiaxed hexagonal grains of about 600 nm formed in the sample SPSed at 1450 °C, together with the additive phases at the  $\alpha$ - $\text{Si}_3\text{N}_4$  grain boundaries, shown in Fig. 2a. By contrast, the uniform interlock microstructure of the elongated  $\beta$ - $\text{Si}_3\text{N}_4$ , with 500 nm in width and 3000 nm in length, is developed in the sample SPSed at 1600 °C without any secondary crystalline phase, shown in Fig. 2b.

A typical back scattering electron micrograph of the polished surface of the sample SPSed at 1600 °C is shown in Fig. 3a. It indicates that fully dense and uni-

form interlock microstructure of the elongated  $\beta$ - $\text{Si}_3\text{N}_4$  was obtained in this sample. It consists of two phase regions, the elongated dark region and the white region. Based on the results from XRD analysis and the compositions obtained by the quantitative EDS analysis, we confirmed that the dark region belongs to the  $\beta$ - $\text{Si}_3\text{N}_4$  phase. The white region is the glass phase formed from the residual additives at the boundaries of the  $\beta$ - $\text{Si}_3\text{N}_4$  grains. The typical EDS results for the dark and white regions are shown in Figs. 3b and 3c. The EDS results from larger elongated  $\beta$ - $\text{Si}_3\text{N}_4$  dark region may be more precise, which contains the elements Al, Zr, Y and O (Fig. 3b). It is reasonable to believe that these elements from the additives can diffuse into  $\beta$ - $\text{Si}_3\text{N}_4$  phase, forming  $\beta$ - $\text{Si}_3\text{N}_4$  solid solution. The large amount of Si and N appeared in the glass phase at the grain boundary. However, EDS is probably affected by  $\beta$ - $\text{Si}_3\text{N}_4$  matrix due to the very thin glass layer (about 80 nm).

The phase transformation behaviour during the densification can be explained by considering the distinct types of grain boundary phase [11]. The  $\text{Al}_2\text{O}_3$  and YSZ additive phases,  $\alpha$ - $\text{Al}_2\text{O}_3$ , m- $\text{ZrO}_2$  and t- $\text{ZrO}_2$  around  $\text{Si}_3\text{N}_4$  phase were kept as the mixed powder sintered at 1450 °C. However, they form the liquid glass phase at the grain boundary of  $\text{Si}_3\text{N}_4$  according to the  $\text{ZrO}_2$ - $\text{Al}_2\text{O}_3$ - $\text{SiO}_2$  phase diagram [27] as the mixed powder was sintered at 1600 °C by the reaction with the  $\text{SiO}_2$  (2 wt.%) covering the  $\text{Si}_3\text{N}_4$  particles. Silica layer may exist in the starting  $\text{Si}_3\text{N}_4$  powders provided by the supplier. Sintering at this temperature causes grains growth of elongated  $\beta$ - $\text{Si}_3\text{N}_4$  resulting from the diffusion-dominated solution-precipitation process. The melted glass has enough fluidity to dissolve the  $\alpha$ - $\text{Si}_3\text{N}_4$  grains, but  $\beta$ - $\text{Si}_3\text{N}_4$  grains precipitated from the melt at this temperature. Super saturation provides the driving force for fast nucleation of  $\beta$ - $\text{Si}_3\text{N}_4$  crystallites. Coalescence of precipitated  $\beta$ - $\text{Si}_3\text{N}_4$  crystallites speeds up the growth of elongated  $\beta$ - $\text{Si}_3\text{N}_4$  grains instead of the slower atomic diffusion since it is energetically favourable as it indirectly reduces the supersaturation of dissolved  $\text{Si}_3\text{N}_4$ .



**Figure 2.** SEM images of the fracture surfaces for the samples SPSed at: a) 1450 °C and b) 1600 °C for 15 min

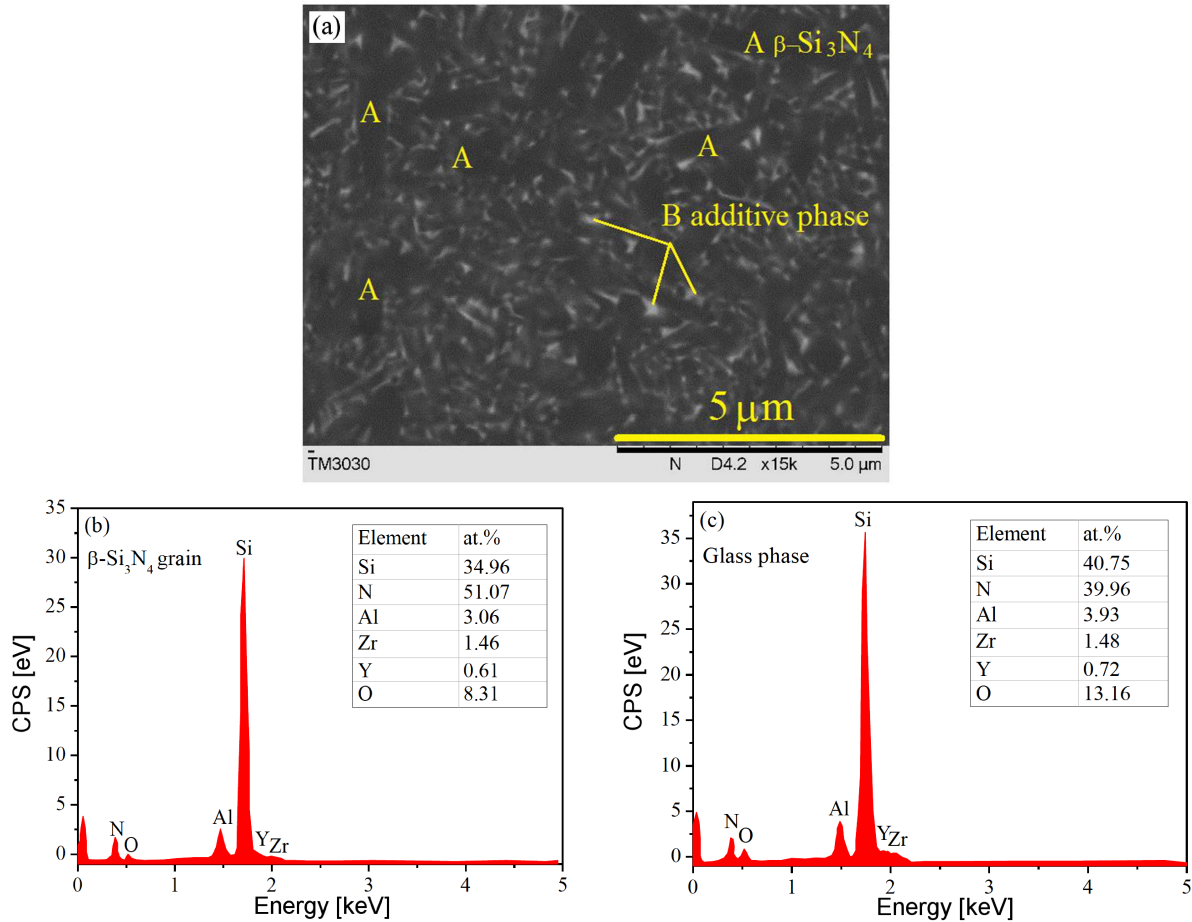


Figure 3. Typical backscattered electron micrograph (a), the EDS images and analysis results for the elongated dark region ( $\beta$ -Si<sub>3</sub>N<sub>4</sub> phase) (b) and the white region (glass phase) (c) in the micrograph of the polished surface of the sample SPSed at 1600 °C for 15 min

Table 1. The relative content of Al<sub>2</sub>O<sub>3</sub> and MgO at different points shown in Fig. 7

Sample	$\rho$ [g/cm <sup>3</sup> ]	$H_v$ [GPa]	$K_{IC}$ [MPa m <sup>1/2</sup> ]	Phase
Si <sub>3</sub> N <sub>4</sub> at 1450 °C	3.255	18.15	3.39	$\alpha$ -Si <sub>3</sub> N <sub>4</sub> + $\beta$ -Si <sub>3</sub> N <sub>4</sub> + $\alpha$ -Al <sub>2</sub> O <sub>3</sub> + m-ZrO <sub>2</sub> + t-ZrO <sub>2</sub>
Si <sub>3</sub> N <sub>4</sub> at 1650 °C	3.289	16.13	6.75	$\beta$ -Si <sub>3</sub> N <sub>4</sub> + Glass

### 3.3. Hardness and fracture toughness

Hardness and fracture toughness were determined using indentation technique. Figure 4 shows a typical

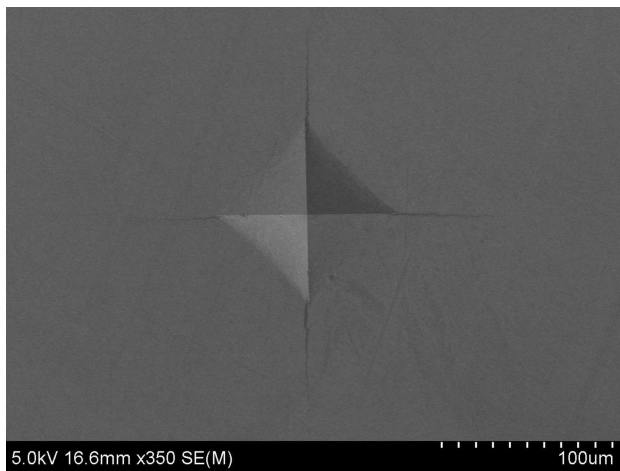


Figure 4. Vickers indent on of the SPSed Si<sub>3</sub>N<sub>4</sub> at 1600 °C for 15 min with 6.0 wt.% Al<sub>2</sub>O<sub>3</sub> and 6.0 wt.% YSZ

Vickers fingerprint on the sample SPSed at 1600 °C for 15 min. The Vickers hardness and fracture toughness of the obtained silicon nitride ceramics in this work are 18.15 GPa and 3.39 MPa m<sup>1/2</sup> for the ceramics SPSed at 1450 °C, and 16.13 GPa and 6.75 MPa m<sup>1/2</sup> for the ceramics SPSed at 1600 °C, respectively (Table 1). The higher Vickers hardness but lower fracture toughness in the sample SPSed at 1450 °C is due to its  $\alpha$ -Si<sub>3</sub>N<sub>4</sub> main phase with weak bonding strength to crystalline Al<sub>2</sub>O<sub>3</sub> and YSZ additives. On the other hand, the slightly lower Vickers hardness but much higher fracture toughness in the sample SPSed at 1600 °C is due to the sample's pure  $\beta$ -Si<sub>3</sub>N<sub>4</sub> phase having strong bonding strength with the glass formed by Al<sub>2</sub>O<sub>3</sub> and YSZ additives. It is known that the hardness of  $\alpha$ -Si<sub>3</sub>N<sub>4</sub> is higher than that of  $\beta$ -Si<sub>3</sub>N<sub>4</sub> [24], while  $\beta$ -Si<sub>3</sub>N<sub>4</sub> phase shows better fracture toughness [10]. The sample SPSed at 1600 °C for 15 min using Al<sub>2</sub>O<sub>3</sub> and yttria-stabilized zirconia additives shows relatively good mechanical properties with Vickers hardness of 16.13 GPa and fracture toughness



of 6.75 MPa m<sup>1/2</sup> as compared to other literature reports. It is reported that the Vickers hardness of 11 GPa and toughness of 5.6 MPa m<sup>1/2</sup> were obtained for Si<sub>3</sub>N<sub>4</sub> by SPS using BaCO<sub>3</sub>, SiO<sub>2</sub> and Al<sub>2</sub>O<sub>3</sub> sintering additives [21]. The Vickers hardness of 6–12 GPa and fracture toughness of 3.7–6.2 MPa m<sup>1/2</sup> were obtained for Si<sub>3</sub>N<sub>4</sub> by hot-pressing using ZrO<sub>2</sub> and Al<sub>2</sub>O<sub>3</sub> as sintering additives [22]. The Vickers hardness of 14.92 GPa and fracture toughness of 6.44 MPa m<sup>1/2</sup> were reported for ceramics fabricated by microwave sintering using Al<sub>2</sub>O<sub>3</sub>, Y<sub>2</sub>O<sub>3</sub> and MgO as sintering additives [28].

#### IV. Conclusions

In this work, we have reported that a nearly fully dense β-Si<sub>3</sub>N<sub>4</sub> ceramics with excellent mechanical properties was fabricated by spark plasma sintering (SPS). The following conclusions could be drawn:

- The fully dense β-Si<sub>3</sub>N<sub>4</sub> ceramics with interlock microstructure with elongated grains was fabricated using α-Si<sub>3</sub>N<sub>4</sub> powder and Al<sub>2</sub>O<sub>3</sub> and yttria-stabilized zirconia (YSZ with 3 mol% Y<sub>2</sub>O<sub>3</sub>) as sintering additives.
- The Al<sub>2</sub>O<sub>3</sub> and YSZ additive phases form the liquid glass phase at the grain boundary of Si<sub>3</sub>N<sub>4</sub> at sintering temperature of 1600 °C by the reaction with the SiO<sub>2</sub> covering the Si<sub>3</sub>N<sub>4</sub> particles in the starting powders.
- The β-Si<sub>3</sub>N<sub>4</sub> ceramics with interlock microstructure with elongated grains was obtained at 1600 °C by mechanism of dissolution-precipitation of the primary α-Si<sub>3</sub>N<sub>4</sub> grains, showing excellent mechanical properties: Vickers hardness of 16.15 GPa and fracture toughness *K<sub>IC</sub>* of 6.75 MPa m<sup>1/2</sup>.

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